

/ Descriptions

VRW056 ММ Ё QSQ æ Ñ ç s ll 1 Silicon NPN transistor in a SOT-23 Plastic Package.

/ Features

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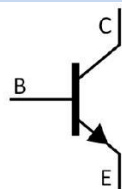
Low noise and high power gain.

/ Applications

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low noise amplifier at VHF, UHF and CATV band applications.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2 χ Emitter PIN 3 χ Collector

/ h_{FE} Classifications & Marking

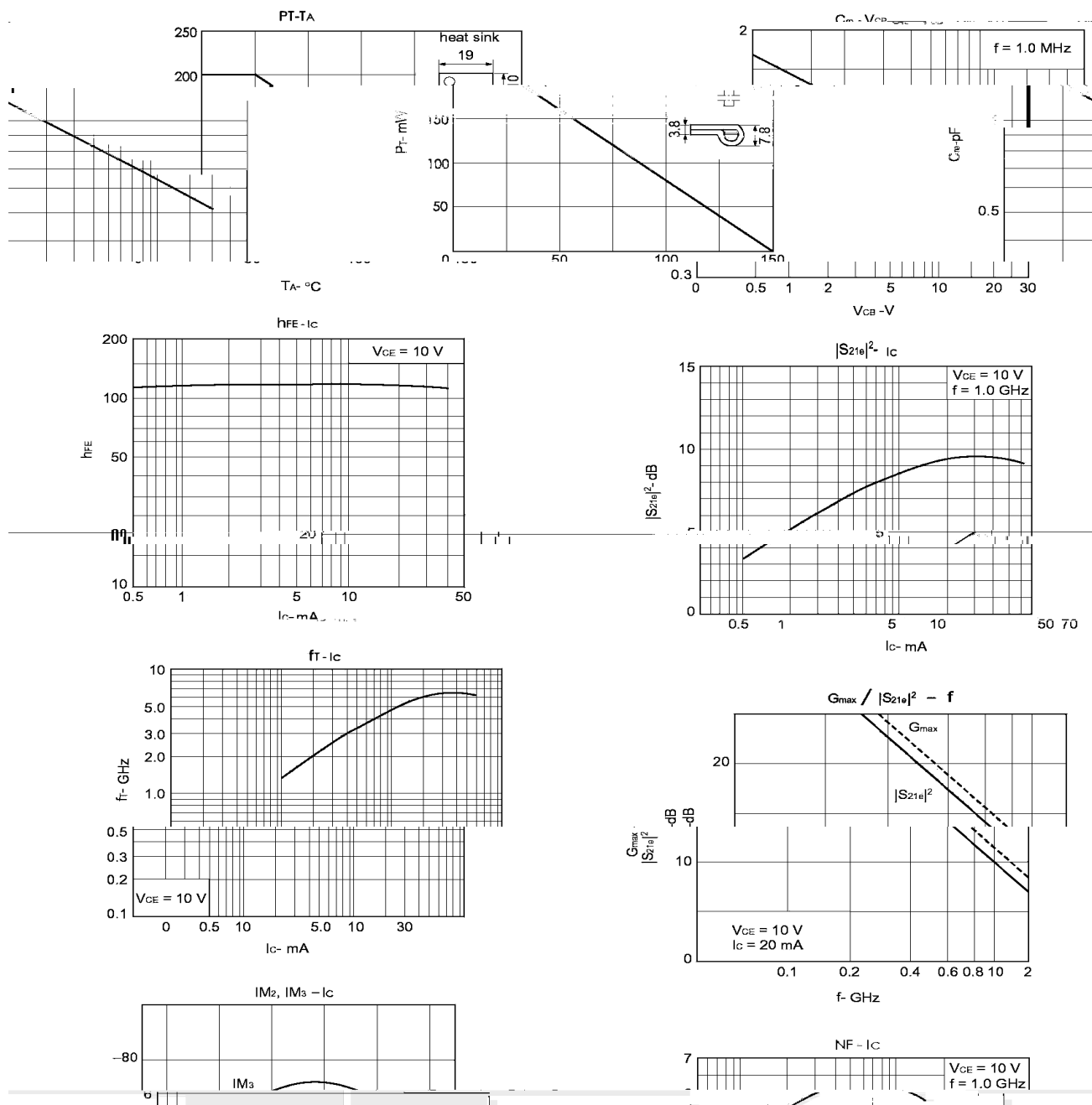
h _{FE} Classifications Symbol	Q	R	S	T
h _{FE} Range	50 100	80 160	125 250	200 330
Marking	HR23	HR24	HR25	HR26

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	20	V
Collector to Emitter Voltage	V_{CEO}	12	V
Emitter to Base Voltage	V_{EBO}	3.0	V
Collector Current	I_C	100	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

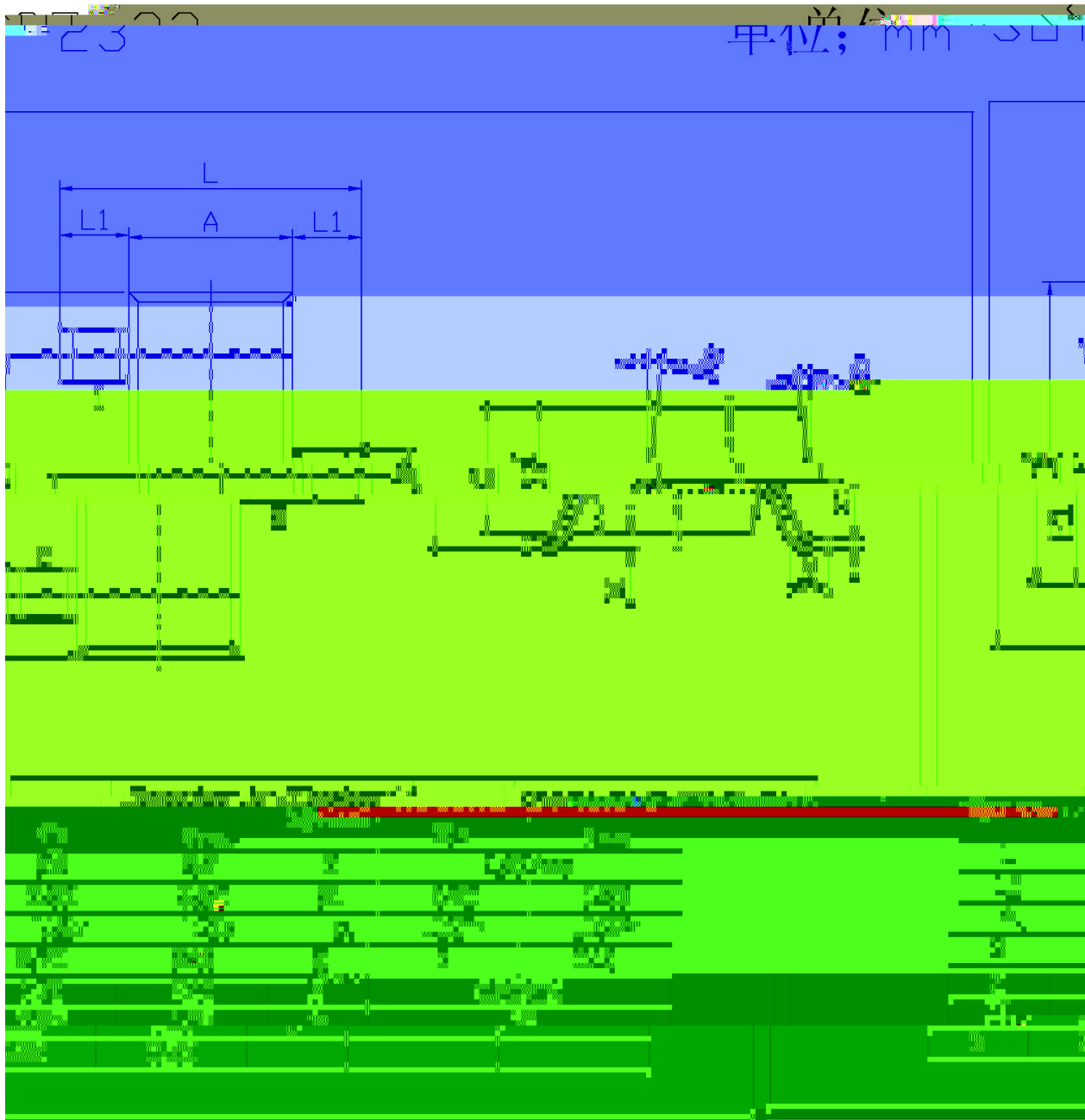
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=10V$ $I_E=0$			1.0	μA

TD 8580

/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



公司代码

K 公司代码

U56 产品代码

Note:

K 公司代码

U56 产品代码

() / Temperature Profile for IR Reflow Soldering(Pb Y